

UNISONIC TECHNOLOGIES CO., LTD

UT3310 Preliminary Power MOSFET

P-CHANNEL ENHANCEMENT MODE POWER MOSFET

■ DESCRIPTION

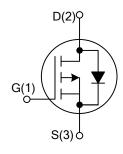
The UTC **UT3310** is a P-channel enhancement mode Power MOSFET. The UTC **UT3310** uses advanced technology to provide customers with fast switching, low on-resistance and cost-effectiveness.

The UTC **UT3310** is generally applied in low voltage and battery power applications.

■ FEATURES

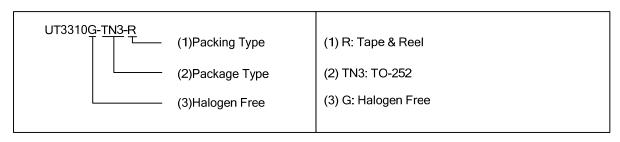
- * Gate Drive Capability: 2.5V
- * Simple Drive Requirement

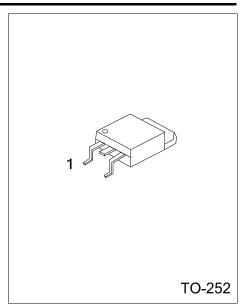
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Dooking	
Ordering Number		1	2	3	Packing	
UT3310G-TN3-R	TO-252	G	D	S	Tape Reel	





■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Drain to Source Voltage	V_{DSS}	-20	V
Gate to Source Voltage	V_{GSS}	±12	V
Continuous Drain Current (T _A =25°C, V _{GS} =10V)	I _D	-10	Α
Pulsed Drain Current	I _{DM}	-24	Α
Total Power Dissipation (T _A =25°C)	P_{D}	25	W
Linear Derating Factor		0.01	W/°C
Junction Temperature	T_J	150	$^{\circ}\mathbb{C}$
Ambient Operating Temperature	T _{OPR}	-55 ~ +150	$^{\circ}$
Storage Temperature	T _{STG}	-55 ~ + 150	$^{\circ}\mathbb{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	5.0	°C/W

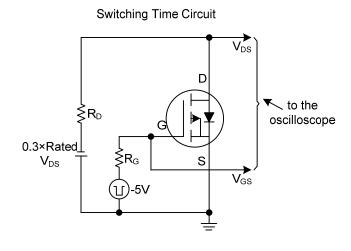
■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

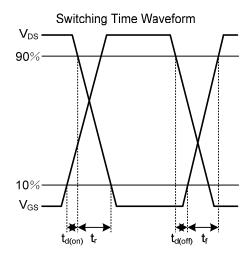
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	OFF CHARACTERISTICS							
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-20			V	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_{J}$	Reference to 25°C, I _D =-1mA		-0.1		V/°C	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain-Source Leakage Current	I _{DSS}	V_{DS} =-20V, V_{GS} =0V			-1	μΑ	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate-Source Leakage Current	I_{GSS}	V _{DS} =0V ,V _{GS} =±12V			±100	nA	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$								
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	-0.5			V	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain-Source On-State Resistance	В	V _{GS} =-4.5V, I _D =-2.8A			150	mΩ	
Input Capacitance		NDS(ON)	V _{GS} =-2.5V, I _D =-2.0A			250	mΩ	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	DYNAMIC PARAMETERS							
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Input Capacitance	C _{ISS}			300		pF	
	Output Capacitance	Coss	V_{DS} =-6V, V_{GS} =0V,f =1.0MHz		180		pF	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Reverse Transfer Capacitance	C _{RSS}			60		pF	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	SWITCHING PARAMETERS							
	Total Gate Charge (Note2)	Q_{G}			6		nC	
Turn-ON Delay Time (Note2) t _{D(ON)} 25 ns	Gate-Source Charge	Q_{GS}	V_{DS} =-6V, V_{GS} =-5V, I_{D} =-2.8A		1.5		nC	
	Gate-Drain Charge	Q_{GD}			0.6		nC	
Turn-ON Rise Time t_R V_{DS} =-6V, V_{GS} =-5V, I_D =-1A 60 ns	Turn-ON Delay Time (Note2)	t _{D(ON)}			25		ns	
	Turn-ON Rise Time	t _R	V_{DS} =-6V, V_{GS} =-5V, I_{D} =-1A		60		ns	
Turn-OFF Delay Time $t_{D(OFF)}$ $R_G=6\Omega, R_D=6\Omega$ 70 ns	Turn-OFF Delay Time	t _{D(OFF)}	$R_G=6\Omega$, $R_D=6\Omega$		70		ns	
Turn-OFF Fall Time t _F 60 ns	Turn-OFF Fall Time	t _F			60		ns	
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS	SOURCE-DRAIN DIODE RATINGS AND CH	IARACTERIS	TICS					
Continuous Source Current (Body Diode) I_S $V_D=V_G=0V$, $V_S=-1.2V$ -10 A	Continuous Source Current (Body Diode)	Is	V _D =V _G =0V , V _S =-1.2V			-10	Α	
Pulsed Source Current (Body Diode) I _{SM} (Note1) -24 A	Pulsed Source Current (Body Diode)	I _{SM}	(Note1)			-24	Α	
Drain-Source Diode Forward Voltage V _{SD} I _S =-10A, V _{GS} =0V (Note2) -1.2 V	Drain-Source Diode Forward Voltage	V_{SD}	I _S =-10A, V _{GS} =0V (Note2)			-1.2	V	

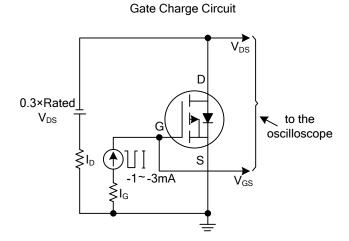
Notes:1. Pulse width limited by safe operating area.

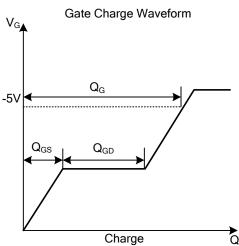
2. Pulse width ≤300us , duty cycle ≤2%.

■ TYPICAL CHARACTERISTICS









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